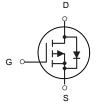


Description

The HSTD36P4LLF6 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

D standard S

TO-252-2L (DPAK)



P-Channel MOSFET

General Features

 $V_{DS} = -40V I_{D} = -40A$

 $R_{DS(ON)}$ < 19 m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HSTD36P4LLF6	TO-252-2L(DPAK)	HXY MOSFET	2500

Absolute Maximum Ratings (Tc=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-40	V
VGS	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	-40	А
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	Continuous Drain Current, V _{GS} @ 10V ¹ -22	
IDM	Pulsed Drain Current ²	d Drain Current ² -140	
P _D @T _C =25°C	Total Power Dissipation ⁴	40.3	W
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
R _θ JA	Thermal Resistance Junction-ambient ¹	66	°C/W
R₀JC	Thermal Resistance Junction-Case ¹	3.1 °C/W	



Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Volta	age	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA -4		-	-	V
Gate-body Leakage current		Igss	V _{DS} = 0V, V _{GS} = ±20V -		-	±100	nA
Zero Gate Voltage Drain Current	TJ=25°C		V _{DS} = -40V, V _{GS} = 0V	-	-	-1	μА
	T _J =100°C	IDSS		-	_	-100	
Gate-Threshold Voltage		V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA -1		-1.5	-2.2	V
		_	V _{GS} = -10V, I _D = -20A	-	13.5	19	
Drain-Source On-Resistance ⁴		R _{DS(on)}	V _{GS} = -4.5V, I _D = -15A	- 19.5 2		25	mΩ
Forward Transconductance ⁴		G fs	V _{DS} = -10V, I _D = -20A	-	44	-	S
Dynamic Characteristics ⁵		l				l	
Input Capacitance		Ciss		-	2525	-	
Output Capacitance		Coss	V _{DS} = -20V, V _{GS} =0V, f =1MHz	-	190	-	pF
Reverse Transfer Capacitance		Crss	1 1141112	-	172	-	
Gate Resistance		Rg	f=1MHz -		10	-	Ω
Switching Characteristics	5	l	1	l	l		
Total Gate Charge		Qg		-	35	-	
Gate-Source Charge		Qgs	V _{GS} = -10V,V _{DS} = -20V, I _D = -20A	-	5.5	-	nC
Gate-Drain Charge		Q _{gd}		-	8	-	
Turn-On Delay Time		t _{d(on)}		-	14.5	-	. ns
Rise Time		tr	$V_{GS} = -10V, V_{DD} = -20V,$	-	20.2	-	
Turn-Off Delay Time		t _{d(off)}	$R_G = 3\Omega$, $I_D = -20A$	-	32	-	
Fall Time		t _f		-	10	-	
Drain-Source Body Diode	Character	istics	I	<u> </u>	1	1	
Diode Forward Voltage ⁴		V _{SD}	I _S = -20A, V _{GS} = 0V	-	-	-1.2	V
Continuous Source Current	T _C =25°C	Is	-	-	-	-40	Α

Note:

- 1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C.
- 2. The EAS data shows Max. rating . The test condition is V_{DD} = -25V, V_{GS} = -10V, L= 0.1mH, I_{AS} = -34A.
- 3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
- 4. The data tested by pulsed , pulse width $\leq 300 us$, duty cycle $\leq 2\%.$
- $5. \ This \ value \ is \ guaranteed \ by \ design \ hence \ it \ is \ not \ included \ in \ the \ production \ test.$



Typical Characteristics

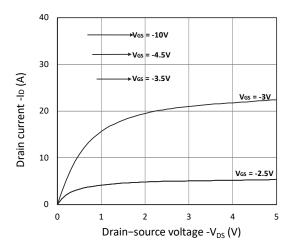


Figure 1. Output Characteristics

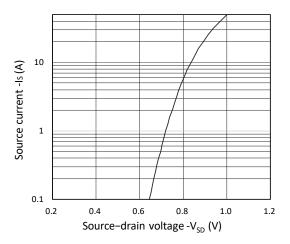


Figure 3. Forward Characteristics of Reverse

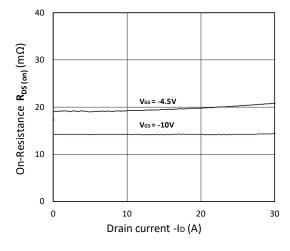


Figure 5. $R_{DS(ON)}$ vs. I_D

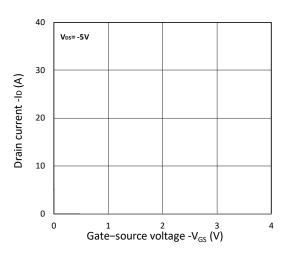


Figure 2. Transfer Characteristics

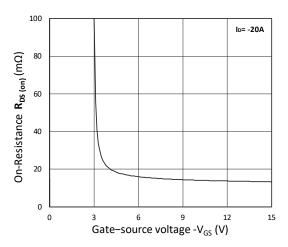


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

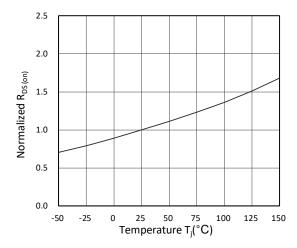


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

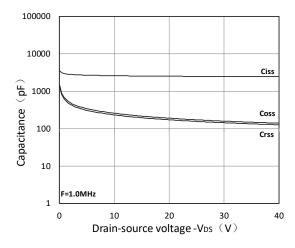


Figure 7. Capacitance Characteristics

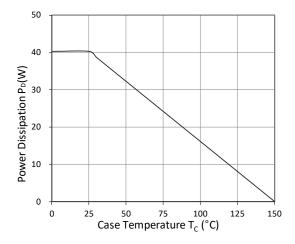


Figure 9. Power Dissipation

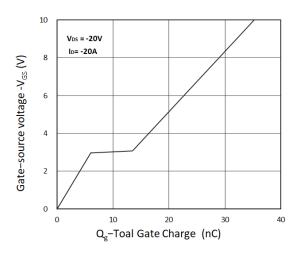


Figure 8. Gate Charge Characteristics

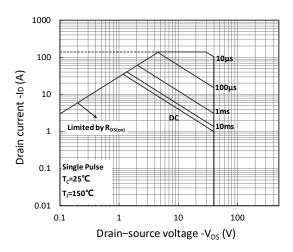


Figure 10. Safe Operating Area

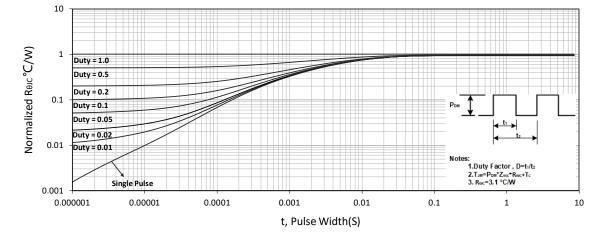


Figure 11. Normalized Maximum Transient Thermal Impedance



Test Circuit

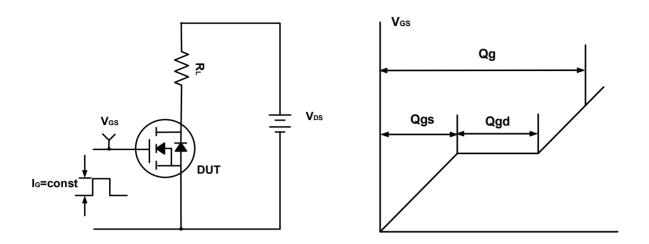


Figure A. Gate Charge Test Circuit & Waveforms

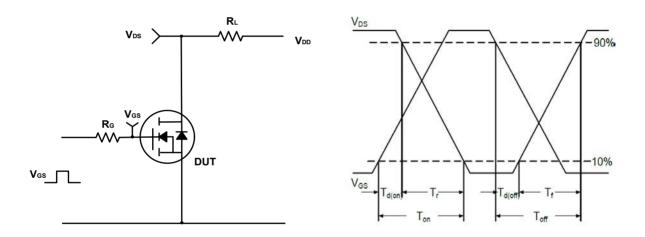


Figure B. Switching Test Circuit & Waveforms

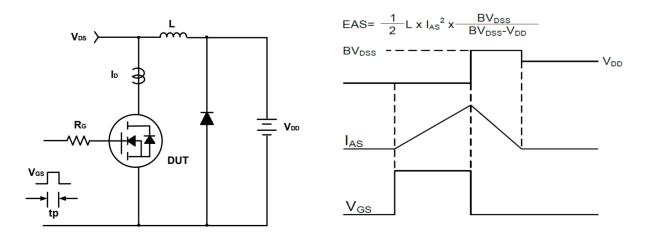
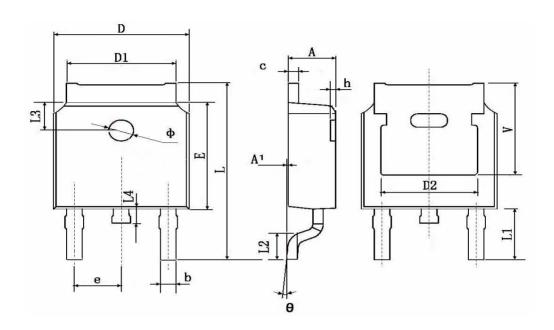


Figure C. Unclamped Inductive Switching Circuit & Waveforms



TO-252-2L(DPAK) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
Α	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3	1.600 TYP.		0.063 TYP.			
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350 TYP.		0.211 TYP.			



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